Carrier relaxation mechanisms in self-assembled (In,Ga)As/GaAs quantum dots: Efficient $P\rightarrow S$ Auger relaxation of electrons

[illegible]

[illegible] 2006; [illegible] 2006

[illegible]

[illegible]

II. CHARACTERISTIC DYNAMICAL PROCESSES OF EXCITED ELECTRONS AND HOLES IN SELF-ASSEMBLED (In,Ga)As/GaAs QUANTUM DOTS

[illegible]

A. Barrier-to-wetting layer carrier capture

[illegible]

B. Carrier capture from the wetting layer into the dot

[illegible]

C. Relaxation of excited carriers within the dot

[illegible] ${}_1(0) = {}_2(0)$

D. Comparison to other calculations for (In,Ga)As/GaAs dots

[8] E. A. [illegible], A. D. A[illegible], [illegible] C[illegible] E [illegible]A[illegible] **26**, 105 [illegible]2005[illegible].

[9] E. A. [illegible] B[illegible], D. A. C[illegible] C[illegible] B **70**, 161305 [illegible]2004[illegible].

[10] E. A. [illegible] B[illegible], D. A. C[illegible]